

Metal Oxidation

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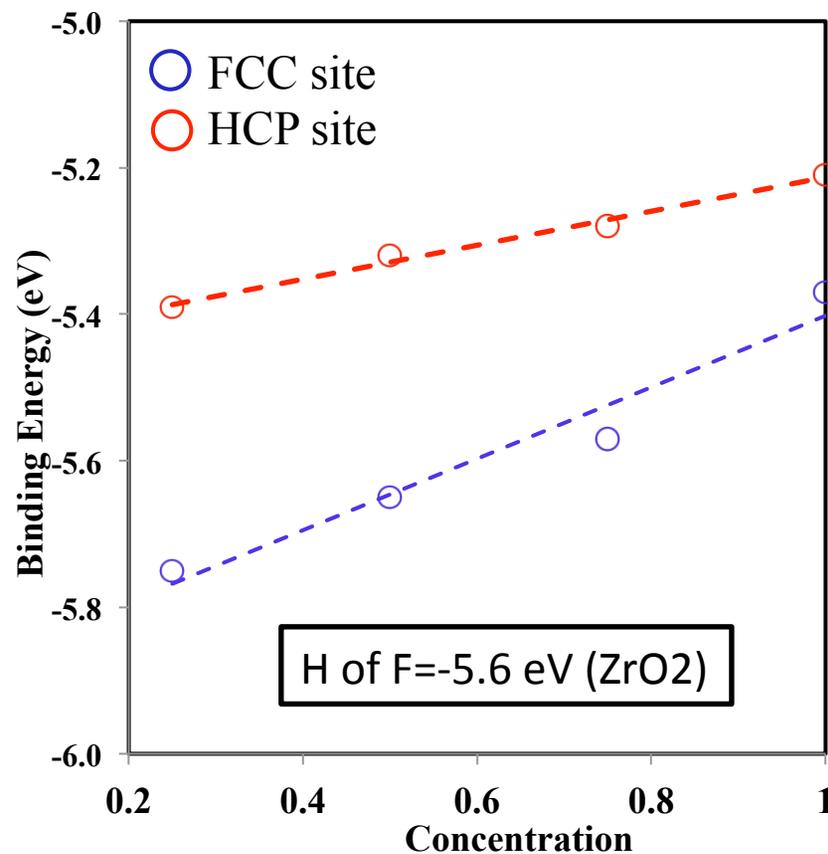
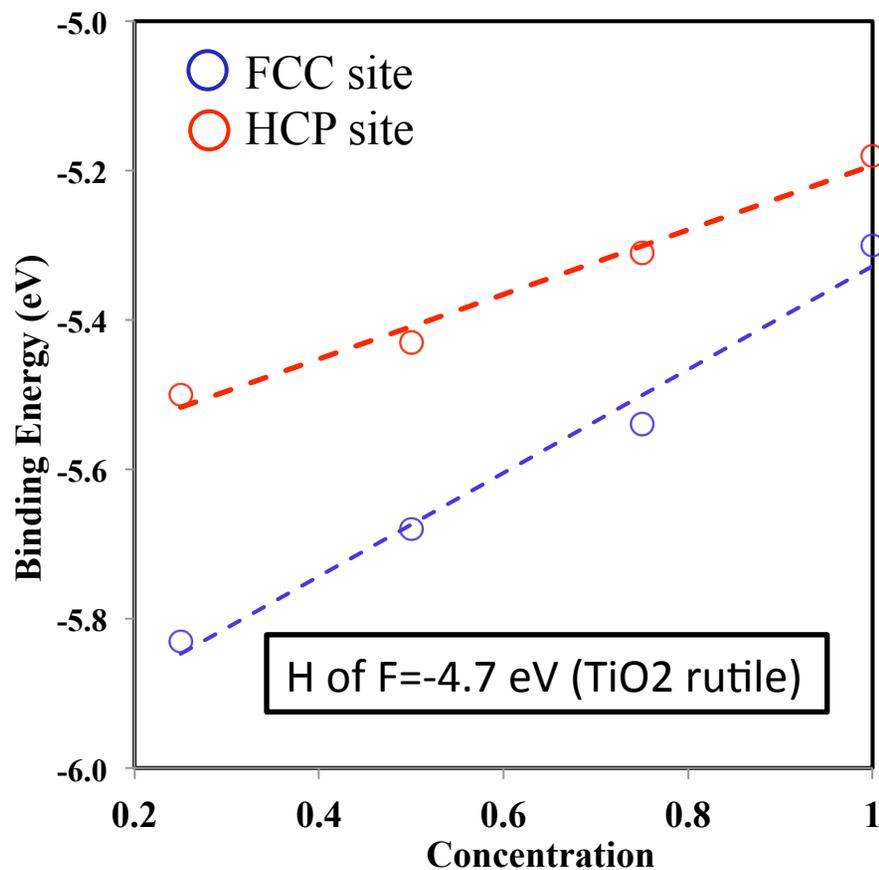
CALTECH-INTEL

Oxygen Binding Energy of Ti(0001) and Zr(0001)

Surfaces

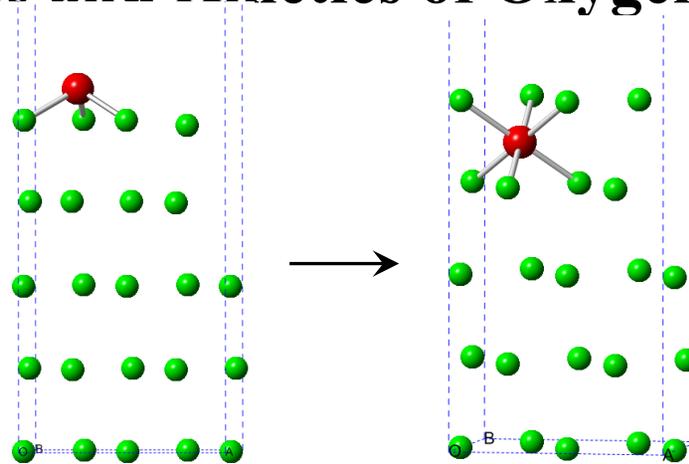
Ti(0001)

Zr(0001)



Surface coverage

The Effect of Surface Oxygen Concentration on the Thermodynamics and Kinetics of Oxygen Penetration (Zr)



Concentration	Reactant	TS	Product (unit: eV)
25 %	0.0		0.68
50 %	0.0	~1.9	0.39
75 %	0.0	~1.5	0.06
100 %	0.0	~1.0	-0.65

Thermodynamically unfavorable for O to penetrate below 100%

Will look at additional layers below the surface

eFF Effective Core Potentials (ECP)

eFF-ECP describes core-valence Pauli interaction, proportional to the overlap between two wave-packets,

$$E_{core-val} \propto S^2$$

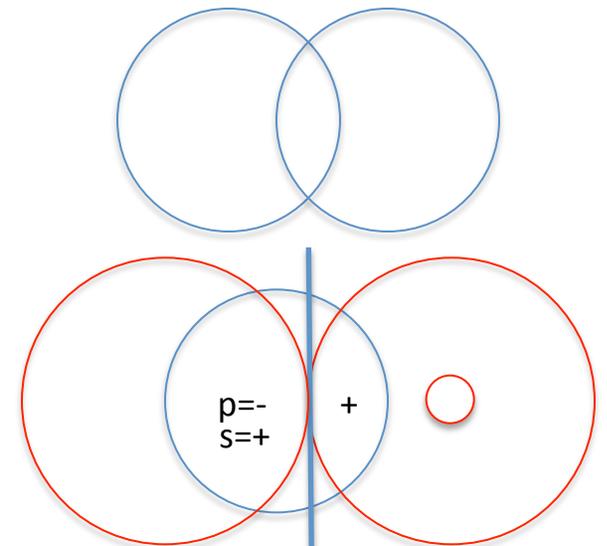
Two types of ECPs developed (and supported in LAMMPS):

1. s-s overlap (e.g. Na, C, Al, Si) – 3 parameters

$$E = a \exp\left(-\frac{br^2}{c+s^2}\right)$$

2. s-p overlap (e.g. C, N, O) – 6 parameters

$$E = a \left(\frac{2}{b/s + s/b} \right) (r - cs)^2 \exp\left[-\frac{d(r - cs)^2}{e + s^2}\right]$$

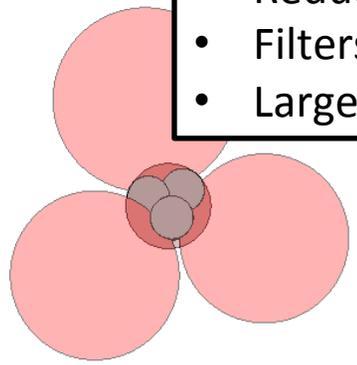


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eFF-ECP e.g. atom representations

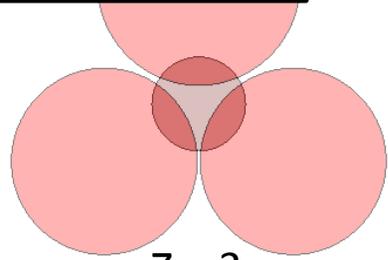
- Reduced number of DOF
- Filters high-frequency core vibrations
- Larger systems and longer timescales

Aluminum



Z = 13

Core+Valence: $1s^2 2s^2 2p^6 3s^2 3p^1$

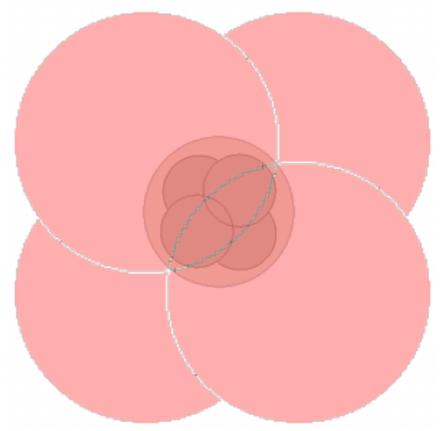


Z = 3

Valence: $3s^2 3p^1$ (4 particles per Al)

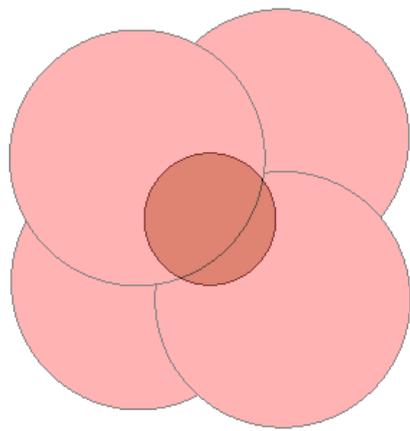
Aluminum core pseudoparticle with valence electrons

Silicon



Z = 14

$1s^2 2s^2 2p^6 3s^2 3p^2$
15 particles per Si!



Z = 4

$3s^2 3p^2$ (5 particles per Si)

Silicon core pseudoparticle with valence electrons

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Si eFF-ECP Pseudopotentials

$$E_{core-elec} = \sum_{i,j} \frac{Z_i Z_j}{R_{ij}} \text{Erf} \left(\frac{\sqrt{2} R_{ij}}{\sqrt{s_{core,i}^2 + s_{elec,j}^2}} \right)$$

$$E_{core-core} = \sum_{i < j} \frac{Z_i Z_j}{R_{ij}} \text{Erf} \left(\frac{\sqrt{2} R_{ij}}{\sqrt{s_{core,i}^2 + s_{core,j}^2}} \right)$$

Multicore interactions supported

- SS-SS
- SS-SP
- SP-SP

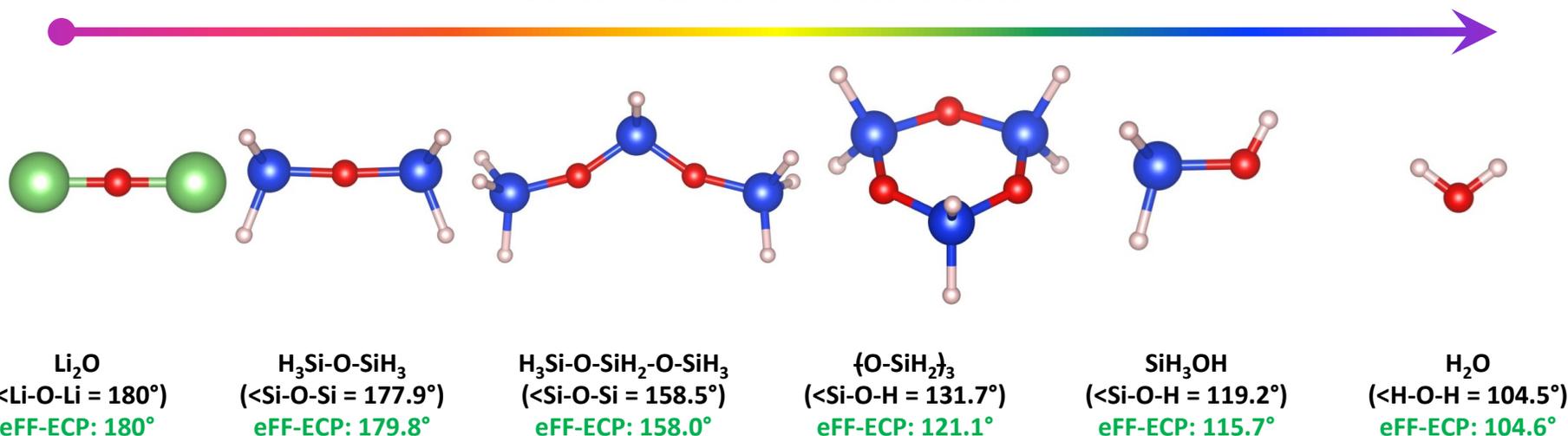
$$E_{core-nuc} = \sum_{i,j} \frac{Z_i Z_j}{R_{ij}} \text{Erf} \left(\frac{\sqrt{2} R_{ij}}{\sqrt{s_{core,j}^2}} \right)$$

$$E_{Pauli_{SS}} = a \text{Exp} \left(\frac{-b r^2}{c + s^2} \right)$$

$$E_{Pauli_{SP}} = a \left(\frac{2}{b/s + s/b} \right) (r - cs)^2 \exp \left[-\frac{d(r - cs)^2}{e + s^2} \right]$$

O-ECP in lone pairs with ionic vs. covalent bonding

From ionic to covalent bonds



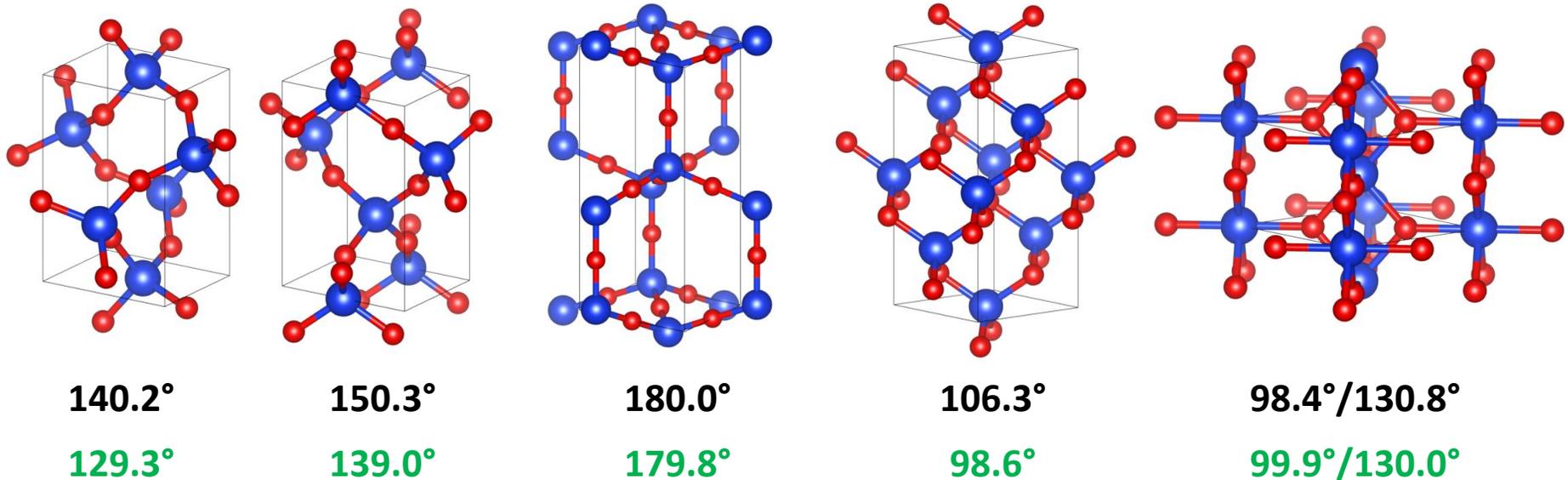
Decreasing Oxygen-centered angle increases covalent bonding (larger repulsion with lone pairs). Focus of ECP is on geometries (angles and bond lengths).

bond length (pm)	Li_2O	$\text{H}_3\text{Si-O-SiH}_3$	$\text{H}_3\text{Si-O-SiH}_2\text{-O-SiH}_3$	$\{\text{O-SiH}_2\}_3$	SiH_3OH	H_2O
bond type	Li-O	Si-O	Si-O	Si-O	Si-O	H-O
Expt.	161.0	163.7	164.4/163.5	165.9	165.9	96.1
eFF-ECP	163.2	165.4	165.0/165.2	171.6	167.3	127.4

O-ECP flexibility of Si-O-Si angle in SiO₂

(α -quartz $\xrightarrow{846\text{ K}}$ β -quartz $\xrightarrow{1140\text{ K}}$ β -tridymite $\xrightarrow{2010\text{ K}}$ β -cristobalite) $\xrightarrow{7.5\sim 8.5\text{ GPa}}$ stishovite

Ground state



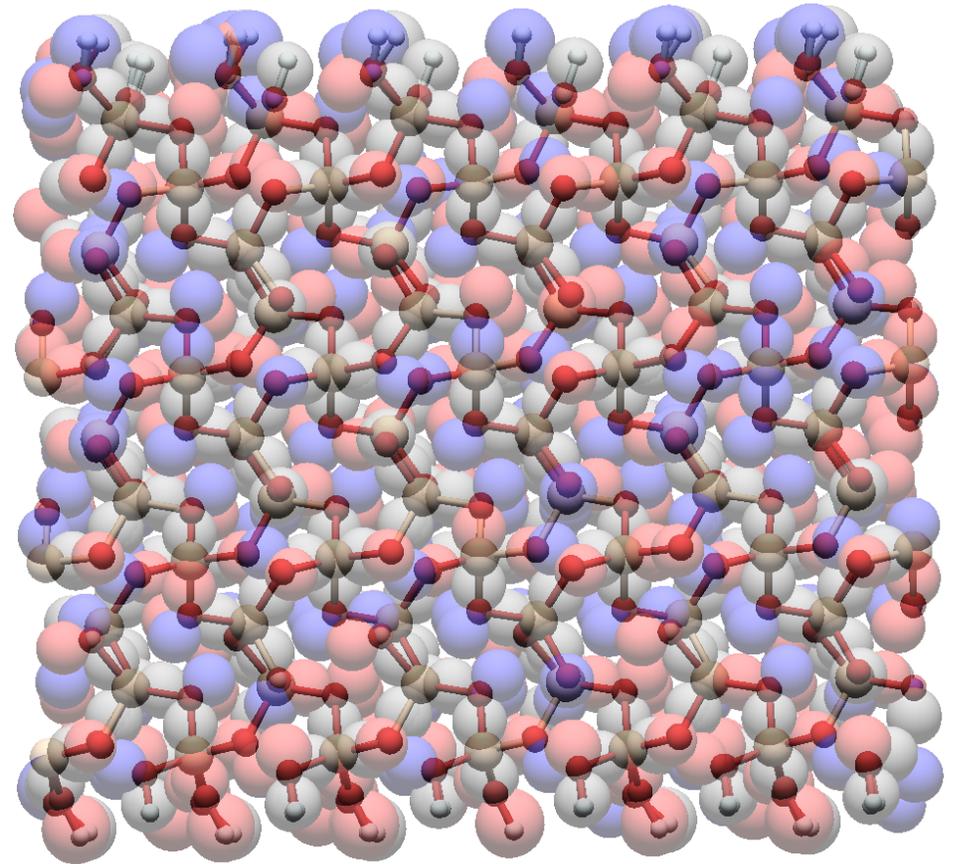
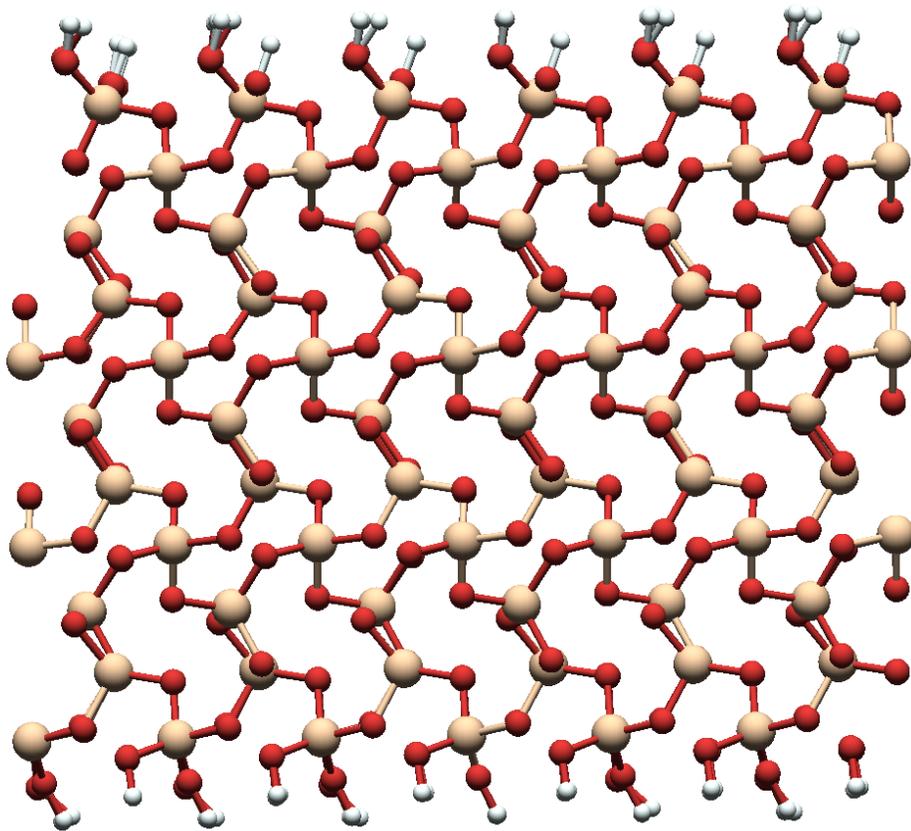
Si-O-Si angle from PBE and eFF-ECP

Si-O bonds in silica possess mixed ionic and covalent nature, and cause a wide range of Si-O-Si angles adopted in various phases. eFF-ECP is able to capture such subtle changes, which demonstrates its capability of describing lone pairs.

Silica Slab Equilibration at 300 K

- Alpha-quartz (001) surface was used, with hydrogen saturating all dangling bonds at both surfaces (oxygen terminated).
- The slab was constructed with dimensions of 46.3 x 48.1 x 42.5 Bohr (the last value is the thickness), with z direction non-periodic and of vacuum.
- Currently we are running nvt equilibration at 300 K (for ~0.1 ps), and the structure is stable.

Snapshot of Silica Slab at 300 K



Next

- Kinetic rates as a function of surface/layer coverage, for both Ti and Zr
- Dynamics with ReaxFF on Ti and Zr oxidation
- kMC approach
- SiO₂ dielectric breakdown